ABSTRACT

The present invention provides a wafer polishing method and a polishing apparatus which are capable of preventing peripheral sags of a wafer due to polishing and then manufacturing the wafer, especially an SOI wafer at a high flatness level. There is provided a wafer polishing method using a polishing apparatus which comprises a rotatable table having a polishing cloth adhered thereon and a polishing head equipped with a wafer holding plate opposing to the table and in which the back surface of the wafer is held by a holding surface of the wafer holding plate and the front surface of the wafer is pressed to and polished by the polishing pad, comprising a polishing step of polishing the front surface of the wafer to a predetermined total polishing stock removal without changing the polishing apparatus, wherein the polishing step is divided into plural sub-steps and a holding position of the wafer in a subsequent sub-step is different from a holding position of the wafer in a previous sub-step.

(12)特許協力条約に基づいて公開された国際出願

(19) 世界知的所有権機関
国際事務局

(43) 国際公開日
2004 年2 月19 日 (19.02.2004)

PCT

(10) 国際公開番号
WO 2004/015752 A1

(51) 国際特許分類[7]: H01L 21/304

(21) 国際出願番号: PCT/JP2003/009658

(22) 国際出願日: 2003 年7 月30 日 (30.07.2003)

(25) 国際出願の言語: 日本語

(26) 国際公開の言語: 日本語

(30) 優先権データ:
特願2002-232693 2002 年8 月9 日 (09.08.2002) JP

(71) 出願人 (米国を除く全ての指定国について): 信越半導体株式会社 (SHIN-ETSU HANDOTAI CO.,LTD.) [JP/JP]; 〒100-0005 東京都 千代田区 丸の内一丁目４番２号 Tokyo (JP).

(72) 発明者; および

(75) 発明者/出願人 (米国についてのみ): 土屋 敏弘 (TSUCHIYA,Toshihiro) [JP/JP]; 〒961-8061 福島県 西白河郡 西郷村大字小田倉字大平１５０ 信越半導体株式会社 半導体白河研究所内 Fukushima (JP).

(74) 代理人: 石原 詔二 (ISHIHARA,Shoji); 〒170-0013 東京都 豊島区 東池袋３丁目７番８号 若井ビル３０２号 Tokyo (JP).

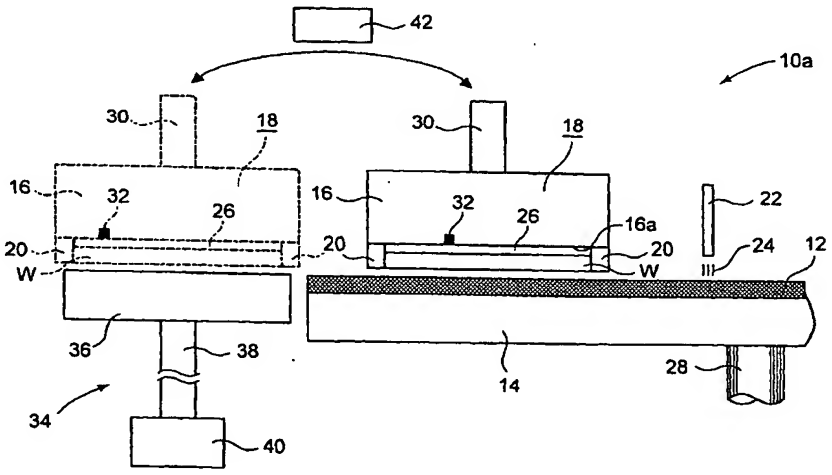
(81) 指定国 (国内): CN, KR, US.

(84) 指定国 (広域): ヨーロッパ特許 (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, RO, SE, SI, SK, TR).

[続葉有]

(54) Title: METHOD AND APPARATUS FOR POLISHING WAFER

(54) 発明の名称: ウェーハの研磨方法及び装置



(57) Abstract: A method and apparatus for polishing a wafer, in which method and apparatus face drops caused by polishing is prevented from occurring and which is capable of producing a wafer with high flatness, particularly, a SOI wafer. The polishing method uses a polishing apparatus that has a rotatable surface plate on the upper face of which abrasive cloth is bonded, and a polishing head provided in a manner opposed to the surface plate and having a wafer holding device. The apparatus performs polishing by pressing the surface of a wafer to the abrasive cloth with the back face of the wafer held on a holding face of the wafer holding device. The polishing method has a polishing step where the surface of the wafer is polished to a total polish margin without changing the polishing apparatus. The method is formed of plural divisional polishing steps that are the divisions of the polishing step, and a holding position of the wafer in late divisional polishing steps is changed to a position different from a holding position in early divisional polishing steps.

(57) 要約: 本発明は、研磨による面ダレを防止し平坦度の高いウエーハ、特にＳＯＩウエーハの製造ができるウエーハの研磨方法及び装置を提供する。本発明は、上面に研磨布を貼付した回転可能な定盤と、該定盤に相対向して設けられウエーハ保持盤を備えた研磨ヘッドとを有し、該ウエーハ保持盤の保持面にウエー

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